**Vishay Semiconductors** 



## Ultrafast Rectifier, 2 A FRED Pt<sup>®</sup>



### MicroSMP (DO-219AD)

Anode O Cathode

### LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS					
I <sub>F(AV)</sub>	2 A				
V <sub>R</sub>	100 V, 200 V				
V <sub>F</sub> at I <sub>F</sub>	0.82 V				
t <sub>rr</sub> (typ.)	33 ns				
I <sub>FSM</sub>	30 A				
T <sub>J</sub> max.	175 °C				
Package	MicroSMP (DO-219AD)				
Circuit configuration	Single				

### **FEATURES**

- · Very low profile typical height of 0.65 mm
- · Ideal for automated placement
- Low forward voltage drop, low power losses
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- For PFC, CRM snubber operation
- AEC-Q101 qualified
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

## **TYPICAL APPLICATIONS**

For use in high frequency, freewheeling, DC/DC converters, PFC, and in snubber industrial and automotive applications.

### **MECHANICAL DATA**

Case: MicroSMP (DO-219AD)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002, meets JESD 201 class 2 whisker test Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS								
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage -	VS-2EQH01HM3	V		100	V			
Feak repetitive reverse voltage -	VS-2EQH02HM3	V <sub>RRM</sub>		200				
Average rectified forward current		I <sub>F(AV)</sub>	T <sub>M</sub> = 137 °C	2	٨			
Non-repetitive peak surge current		I <sub>FSM</sub>	$T_J = 25 \ ^{\circ}C$ , 10 ms sine pulse	30	A			
Operating junction and storage temperatures		T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C			

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25 \text{ °C}$ unless otherwise specified)								
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage,	VS-2EQH01HM3	V <sub>BR</sub> ,	1 1004	100	-	-		
blocking voltage	VS-2EQH02HM3	VR	I <sub>R</sub> = 100 μΑ	200			v	
Forward valtage		VF	I <sub>F</sub> = 2 A	-	0.96	1.05	v	
Forward voltage		v <sub>F</sub>	I <sub>F</sub> = 2 A, T <sub>J</sub> = 150 °C	-	0.82	0.84		
Deveres lockage ourrent		1	$V_{\rm R} = V_{\rm R}$ rated	-	-	1		
Reverse leakage current		IR	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	25	μΑ	
Junction capacitance		CT	V <sub>R</sub> = 200 V	-	6	-	pF	





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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}$	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		33	-			
Reverse recovery time	+	I <sub>F</sub> = 0.5 A, I <sub>R</sub> = 1 A, I <sub>rr</sub> = 0.25 A		-	-	23			
	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	19	-	ns		
		T <sub>J</sub> = 125 °C		-	33	-			
Peak recovery current I <sub>RF</sub>		T <sub>J</sub> = 25 °C	I <sub>F</sub> = 2 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 100 V	-	1.7	-	A		
	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C		-	2.5	-			
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	15	-	nC		
		T <sub>J</sub> = 125 °C		-	34	-			

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and range	storage temperature	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C	
Thermal resistance, junction to mount		R <sub>thJM</sub> <sup>(1)</sup>		-	16	20		
Thermal resistance, junction to ambient		R <sub>thJA</sub>	Device mounted on FR4 PCB, 2 oz. standard footprint	-	160	-	°C/W	
Approximate weight					0.006		g	
VS-2EQH01HM3					2H1			
Marking device	VS-2EQH02HM3		Case style MicroSMP (DO-219AD)	2H2				

#### Note

<sup>(1)</sup> Thermal resistance junction to mount follows JEDEC<sup>®</sup> 51-14 transient dual interface test method (TDIM)

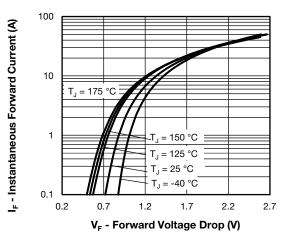


Fig. 1 - Typical Forward Voltage Drop Characteristics

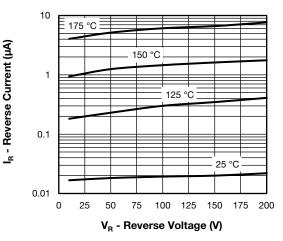


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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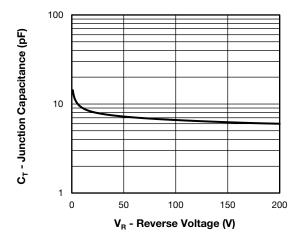


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

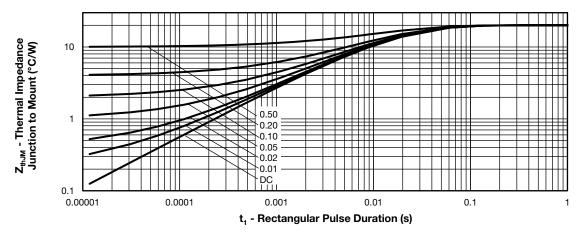
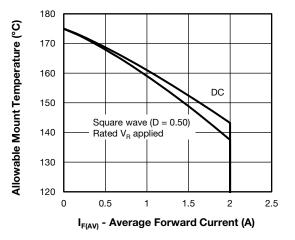
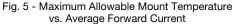


Fig. 4 - Maximum Transient Thermal Impedance, Junction to Mount







Formula used:  $T_M = T_J - (Pd + Pd_{REV}) \times R_{thJM}$ ; Pd = forward power loss =  $I_{F(AV)} \times V_{FM}$  at ( $I_{F(AV)}/D$ ) (see fig. 5); Pd\_{REV} = inverse power loss =  $V_{R1} \times I_R (1 - D)$ ;  $I_R$  at  $V_{R1}$  = rated  $V_R$ 

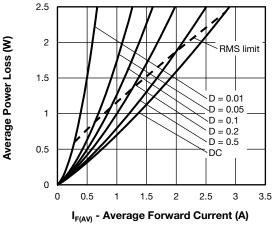


Fig. 6 - Forward Power Loss Characteristics

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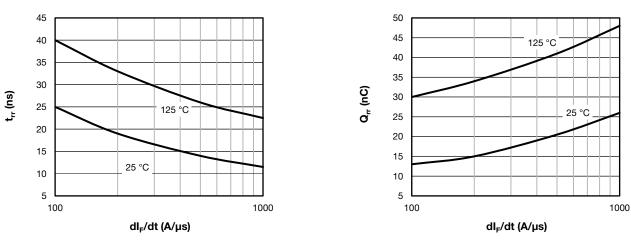


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

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Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

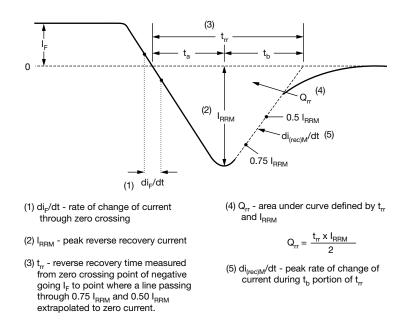
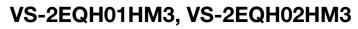


Fig. 9 - Reverse Recovery Waveform and Definitions



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### **ORDERING INFORMATION TABLE**

Device code	VS-	2	Е	Q	н	02	н	М3	
		2	3	4	5	6	7	8	
	2	- Cur	Vishay Semiconductors product Current rating (2 = 2 A) Circuit configuration:						
		- Q =	single o MicroS cess typ	MP pac	kage				
		- Vol	age coo	st recove de (02 = 101 qua	200 V)				
	8	- M3	= halog	en-free,	RoHS-0	complia	nt, and	termina	tions lead (Pt

ORDERING INFORMATION (Example)							
PREFERRED P/N	PREFERRED PACKAGE CODE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-2EQH01HM3/H	Н	4500	7" diameter plastic tape and reel				
VS-2EQH02HM3/H	Н	4500	7" diameter plastic tape and reel				

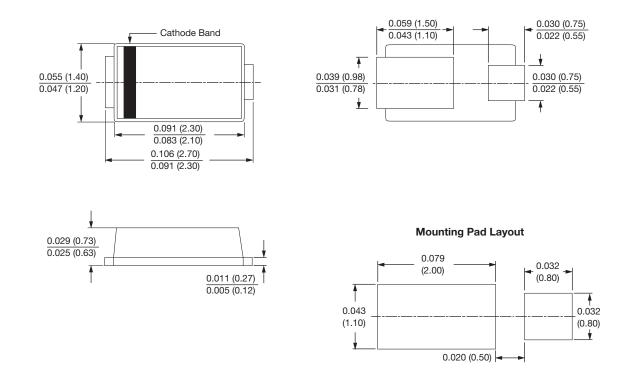
LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?96591					
Part marking information	www.vishay.com/doc?96590					
Packaging information	www.vishay.com/doc?88869					
SPICE model	www.vishay.com/doc?96595					



**Vishay Semiconductors** 

# MicroSMP (DO-219AD), FRED Pt®

### **DIMENSIONS** in inches (millimeters)





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